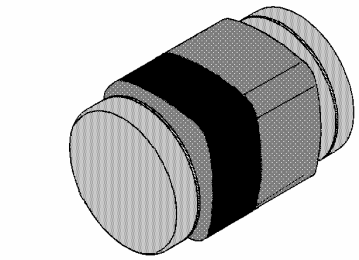
MCL245

SILICON EPITAXIAL PLANAR DIODE

LS-31



Features

- Fast switching diode
- Fits onto SOD 323 / SOT 23 footprints
- Micro Melf package

Absolute Maximum Ratings ($T_a = 25^oC$)

	Symbol	Value	Unit
Reverse Voltage	V_R	220	V
Peak Reverse Voltage	V_{RM}	250	V
Mean Rectified Current Half Wave Rectification with Resistance load at $T_{amb} = 25^oC$ and f/50 H_Z	I_O	200	mA
Maximum Forward Current	I_{FM}	625	mA
Surge Forward Current at t<1s and $T_j = 25^oC$	I_{FSM}	1000	mA
Junction Temperature	T_j	175	^OC
Storage Temperature Range	T_S	-65 to +175	^OC

[1)] Valid provided that electrodes are kept at ambient temperature

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Characteristics at $T_j = 25^oC$

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 200mA$	V_F	-	-	1.5	V
Leakage Current at $V_R = 220V$	I_R	-	-	10	µA
Reverse Breakdown Voltage tested with 100uA Pulses	V_{BR}	250	-	-	V
Capacitance at $V_F = V_R = 0$, f = 1MHz	C_{tot}	-	-	3	pF
Reverse Recovery Time From $I_F = I_R = 20mA$	t_{rr}	-	-	75	ns

Dimensions in mm